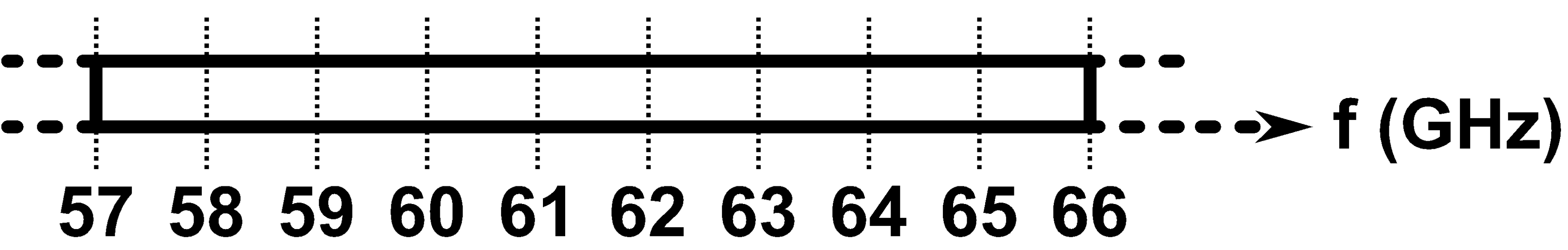


Shunt Characterization Technique of Decoupling Transmission Line for Millimeter-Wave CMOS Amplifier Design

Korkut Kaan Tokgoz, Kimsrun Lim, Kenichi Okada, and Akira Matsuzawa

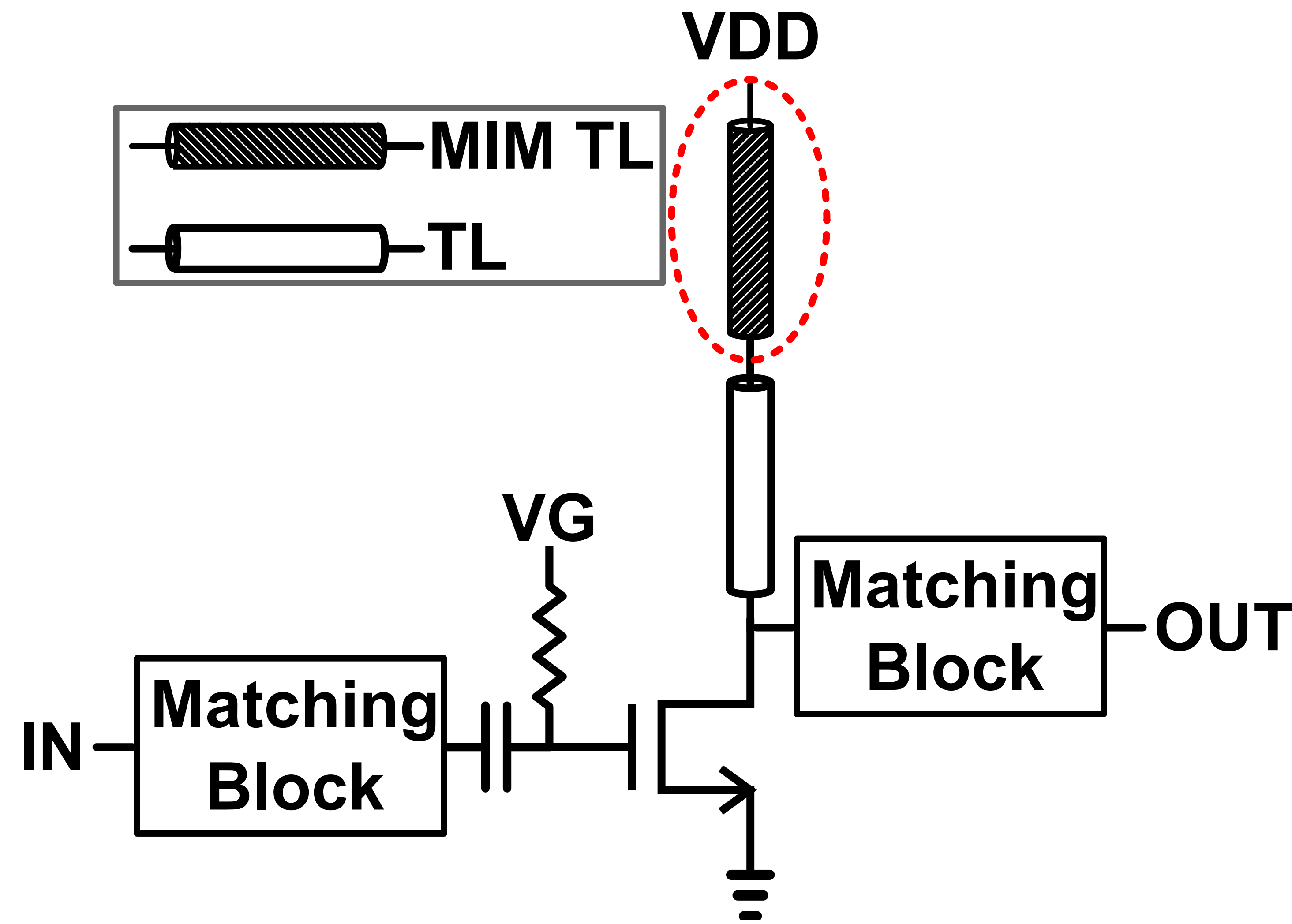
Matsuzawa & Okada Lab, Tokyo Institute of Technology
E-mail: korkut@ssc.pe.titech.ac.jp

1. Motivation



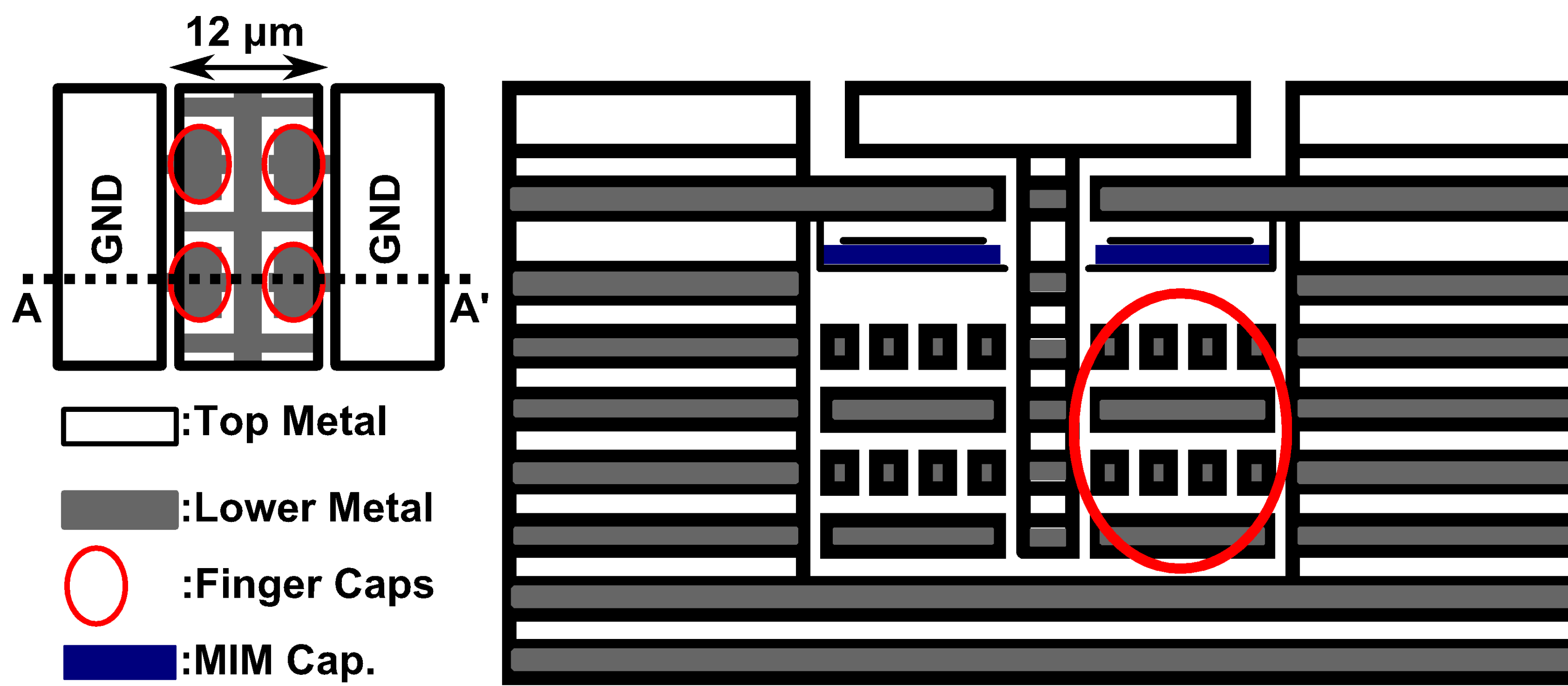
- 60-GHz wireless communication with 9 GHz unlicensed bandwidth
- Wide bandwidth: 2.16 GHz x 4 channels
- Ultra high data rate:
 - 64QAM → 10.56Gbps/ch
 - 64QAM → 42.24Gbps (4-ch bonding)
- Secure communication

Representation of a simple amplifier



- Decoupling of DC and RF:
 - Metal-Insulator-Metal TL
 - Lumped components lacks accuracy
 - More reliable in millimeter-wave

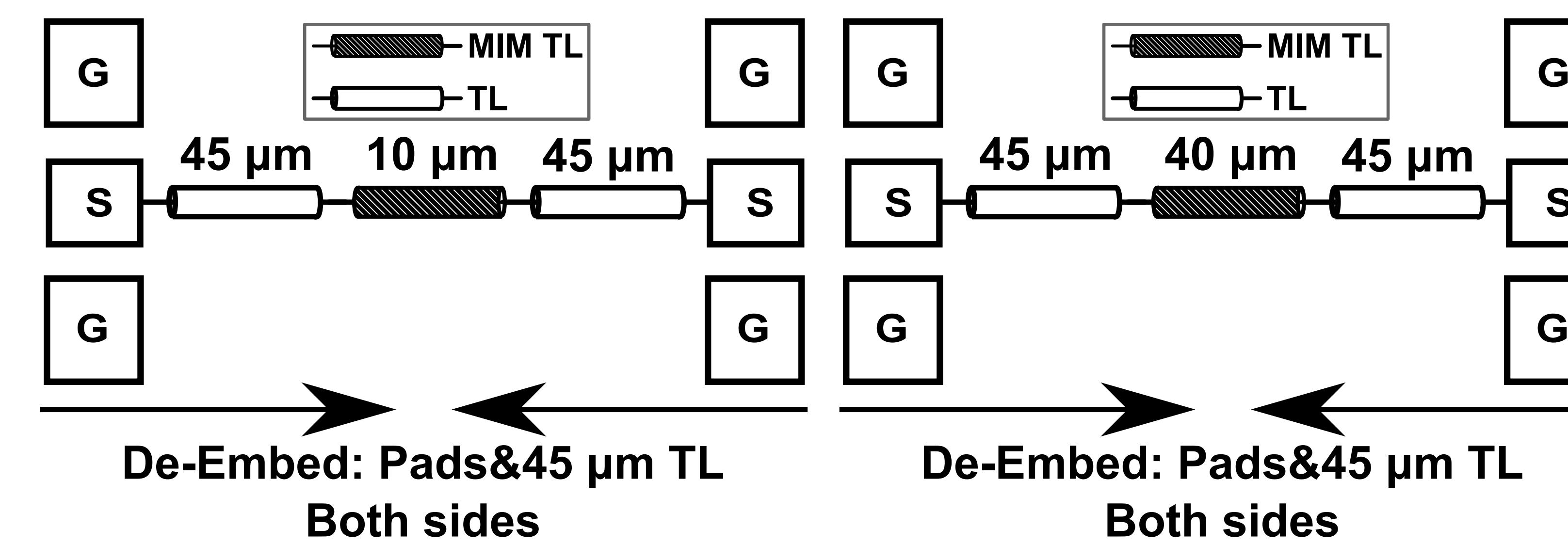
2. MIM Transmission Line



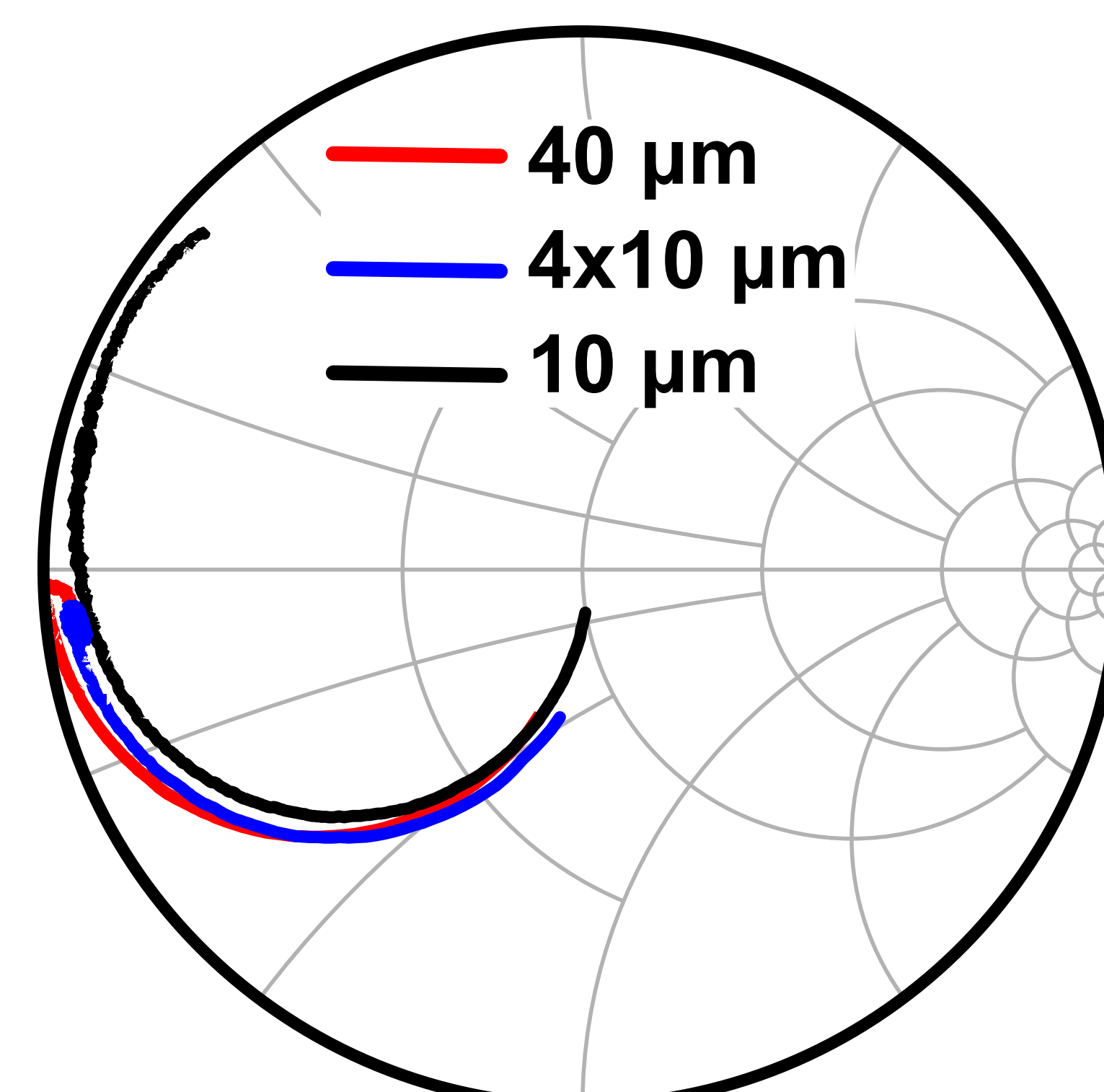
- Desired MIM TL characteristics:
 - Low characteristic impedance (1~3 Ω)
 - High RF loss

Issues:

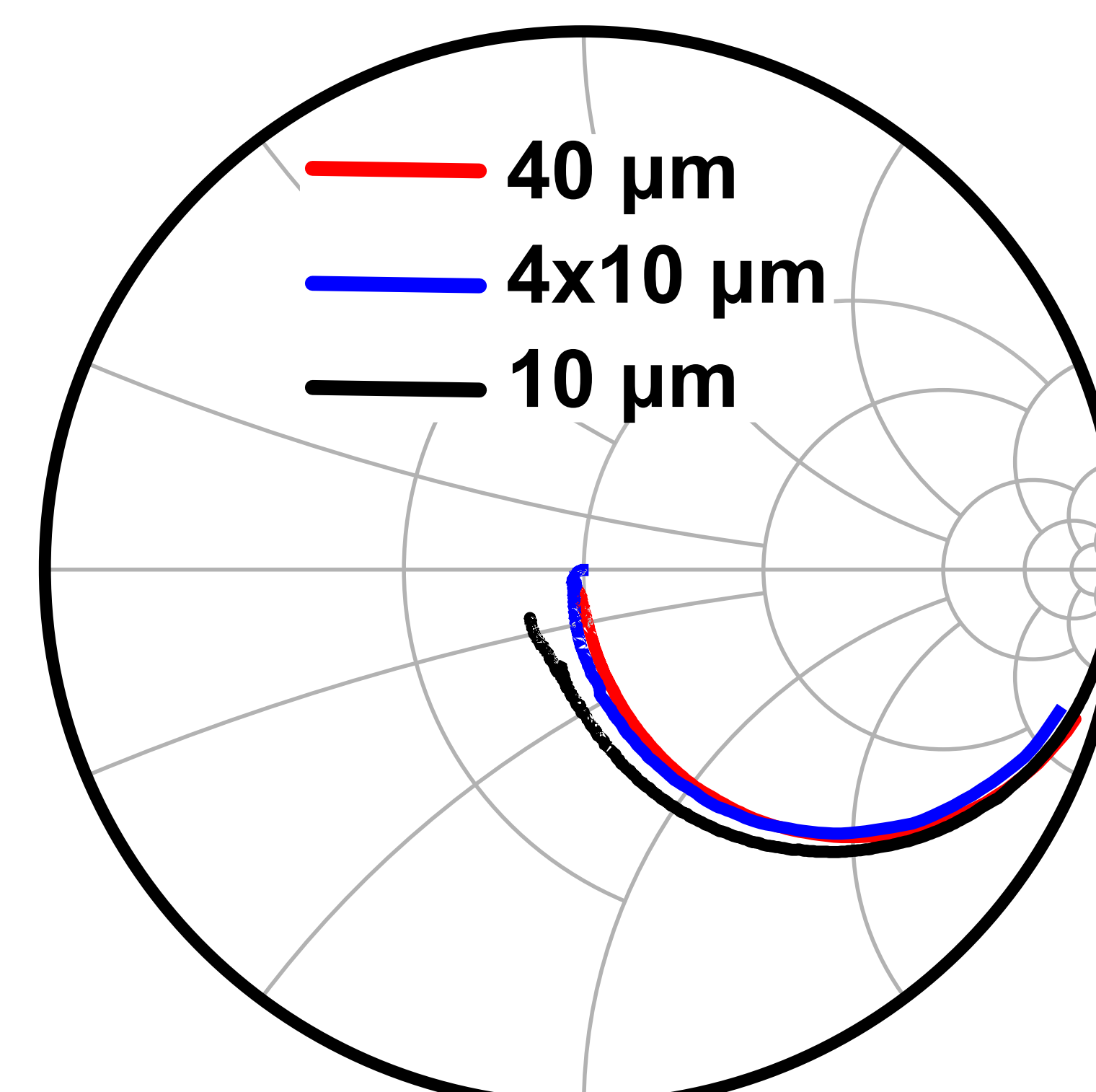
- Direct measurement accuracy



Return Loss

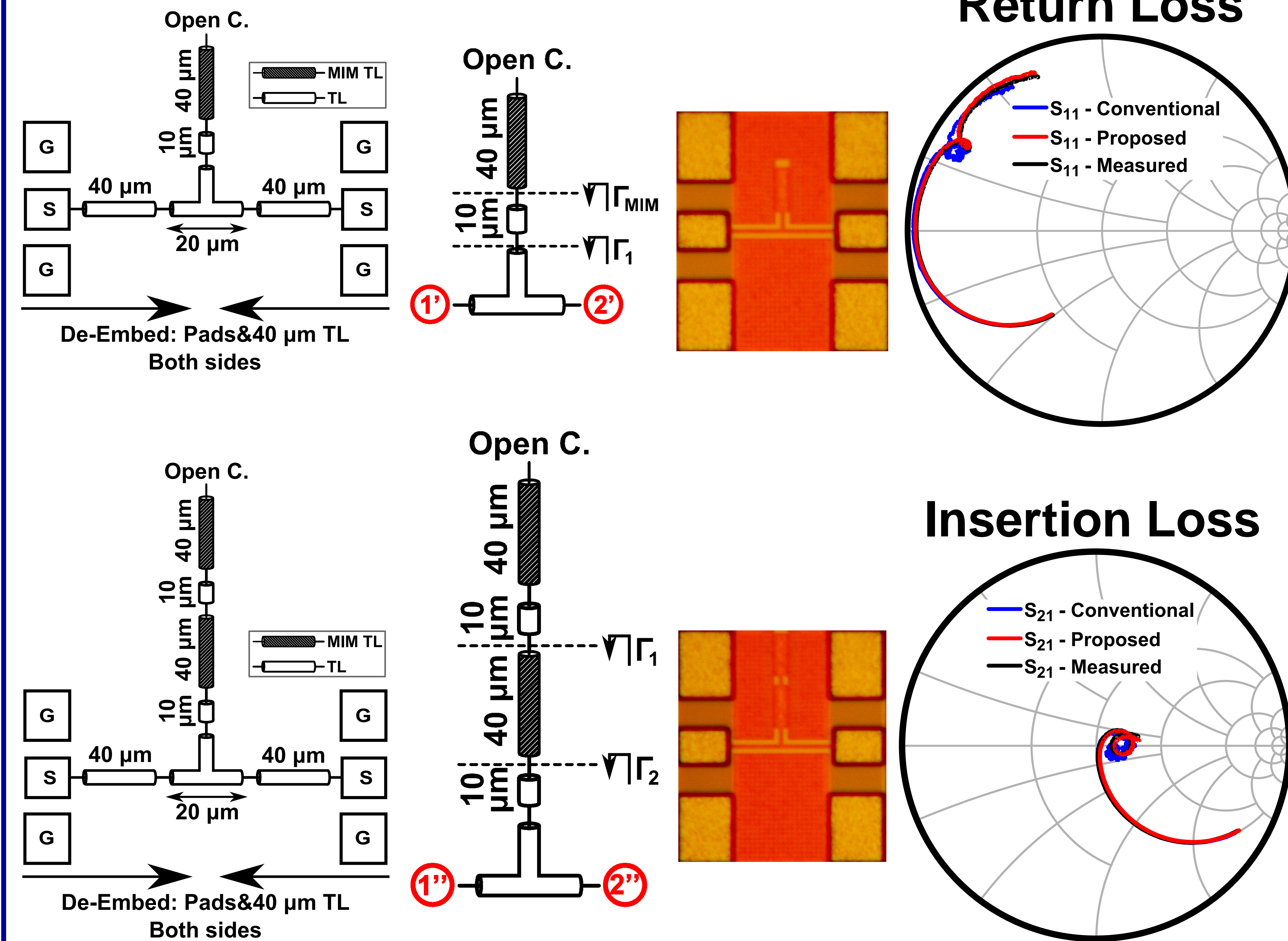


Insertion Loss



3. Shunt Characterization

- Two characterization structures



4. Conclusion

- Metal-insulator-metal decoupling transmission line with very low characteristic impedance
- Inaccuracy in direct measurements
- A shunt characterization method is proposed for increased accuracy
- S-parameters of Metal-insulator-metal transmission line calculated from reflections
- Shunt characterization results show good agreement up to 110 GHz
- Better agreement than conventional approach